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April 1<sup>st</sup>, 2010 Renesas Electronics Corporation

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### DATA SHEET



# NPN SiGe RF ANALOG INTEGRATED CIRCUIT $\mu PA901TU$

## NPN SiGe RF IC IN A 8-PIN LEAD-LESS MINIMOLD

### **DESCRIPTION**

The  $\mu$ PA901TU is a silicon germanium HBT IC designed for the power amplifier of 5.8 GHz cordless phone and other 5.8 GHz applications. This IC consists of two stage amplifiers and has excellent performance, high efficiency, high gain, low power consumption.

The device is packaged in surface mount 8-pin lead-less minimold plastic package.

The device is fabricated with our SiGe HBT process UHS2-HV technology.

### **FEATURES**

Output Power: Pout = 19 dBm @ Pin = -3 dBm, VcE = 3.6 V, f = 5.8 GHz

• Low Power :  $Ic = 90 \text{ mA} @ P_{in} = -3 \text{ dBm}, VcE = 3.6 \text{ V}, f = 5.8 \text{ GHz}$ 

• Single Power Supply Operation : VcE = 3.6 V

· Built-in bias circuit

• 8-pin lead-less minimold (2.0 × 2.2 × 0.5 mm)

#### **APPLICATIONS**

- 5.8 GHz cordless phone
- 5.8 GHz band DSRC (Dedicated Short Range Communication) system
- 5.8 GHz video transmitter

### **ORDERING INFORMATION**

Part Number	Order Number	Quantity	Package	Marking	Supplying Form
μPA901TU	μPA901TU-A	50 pcs (Non reel)	8-pin lead-less	A901	• 8 mm wide embossed taping
μPA901TU-T3	μPA901TU-T3-A	5 kpcs/reel	minimold (Pb-Free)		• Pin 1, Pin 8 face the perforation side of the tape

**Remark** To order evaluation samples, contact your nearby sales office.

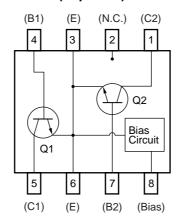
The unit sample quantity is 50 pcs.

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

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### PIN CONNECTIONS AND INTERNAL BLOCK DIAGRAM

### (Top View)



### ABSOLUTE MAXIMUM RATINGS ( $T_A = +25$ °C)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	Vсво	15	V
Collector to Emitter Voltage	Vceo	4.5	٧
Emitter to Base Voltage	VEBO	2	V
Collector Current of Q1	Ic1	75	mA
Collector Current of Q2	Ic2	250	mA
Bias Current	BIAS	25	mA
Total Power Dissipation	Ptot Note	410	mW
Junction Temperature	Tj	150	°C
Storage Temperature	T <sub>stg</sub>	-65 to +150	°C
Operating Ambient Temperature	TA	-40 to +85	°C

**Note** Mounted on  $20 \times 20 \times 0.8$  mm (t) glass epoxy PCB (FR-4)

### THERMAL RESISTANCE ( $T_A = +25$ °C)

Parameter	Symbol	Test Conditions	Ratings	Unit
Channel to Ambient Resistance	Rth (j-a1) Note		150	°C/W
	Rth (j-a2)	Free Air	TBD	°C/W

**Note** Mounted on  $20 \times 20 \times 0.8$  mm (t) glass epoxy PCB (FR-4)

### RECOMMENDED OPERATING RANGE (All Parameter)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Collector to Emitter Voltage	Vce	-	3.6	4.5	V
Total Current	Itotal	-	90	300	mA
Input Power	Pin	-	-3	+5	dBm

2



### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = +25°C) -DC CHARACTERISTICS-

### (1) Q1

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Collector Cut-off Current	Ісво	VcB = 5 V, IE = 0 mA	-	ı	60	nA
Emitter Cut-off Current	ІЕВО	V <sub>EB</sub> = 1 V, I <sub>C</sub> = 0 mA	-	1	120	nA
DC Current Gain	hfe Note	VcE = 3 V, Ic = 6 mA	80	120	160	-
Current Ratio (Ic (set) 1/IBIAS)	CR1	Vce = 3.6 V, Vbe = Vbias = 0.865 V	2	4.5	9	_

### (2) Q2

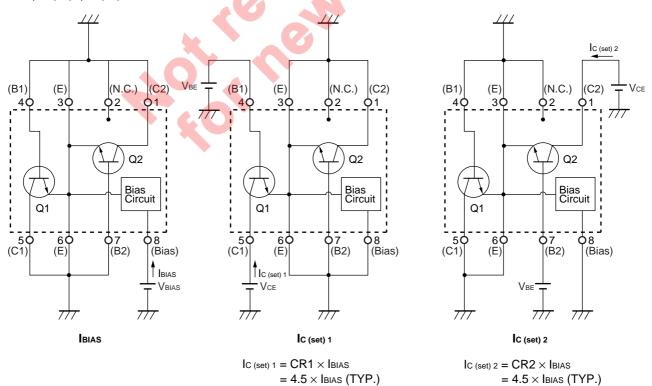
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Collector Cut-off Current	Ісво	Vсв = 5 V, IE = 0 mA	-	1	200	nA
Emitter Cut-off Current	ІЕВО	V <sub>EB</sub> = 1 V, I <sub>C</sub> = 0 mA	<u></u>	_	400	nA
DC Current Gain	hfe Note	Vce = 3 V, Ic = 20 mA	80	120	160	-
Current Ratio (Ic (set) 2/IBIAS)	CR2	VCE = 3.6 V, VBE = VBIAS = 0.865 V	8	10	13	-

### (3) Bias Circuit

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Bias Circuit Current	IBIAS	VBIAS = 0.865 V	-	4	_	mA

**Note** Pulse measurement: PW  $\leq$  350  $\mu$ s, Duty Cycle  $\leq$  2%

### IBIAS, IC (set) 1, IC (set) 2 MEASUREMENT CIRCUIT



The application circuits and their parameters are for reference only and are not intended for use in actual design-ins.



### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = +25°C) -RF CHARACTERISTICS-

### (1) Q1

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Insertion Power Gain (Q1)	S <sub>21e</sub>  ²	VcE = 3.6 V, Ic = 12 mA, f = 5.8 GHz	8.5	10.0	11.5	dB
Maximum Available Power Gain (Q1)	MAG1	VcE = 3.6 V, Ic = 12 mA, f = 5.8 GHz	13.5	15.0	-	dB
Output Power (Q1)	Pout1	VcE = 3.6 V, Ic (set) = 12 mA, f = 5.8 GHz, Pin = -3 dBm	10.2	11.2	-	dBm
Collector Current (Q1)	Icc1	$V_{CE} = 3.6 \text{ V}, \text{ Ic (set)} = 12 \text{ mA},$ $f = 5.8 \text{ GHz}, P_{in} = -3 \text{ dBm}$	-	20	-	mA

### (2) Q2

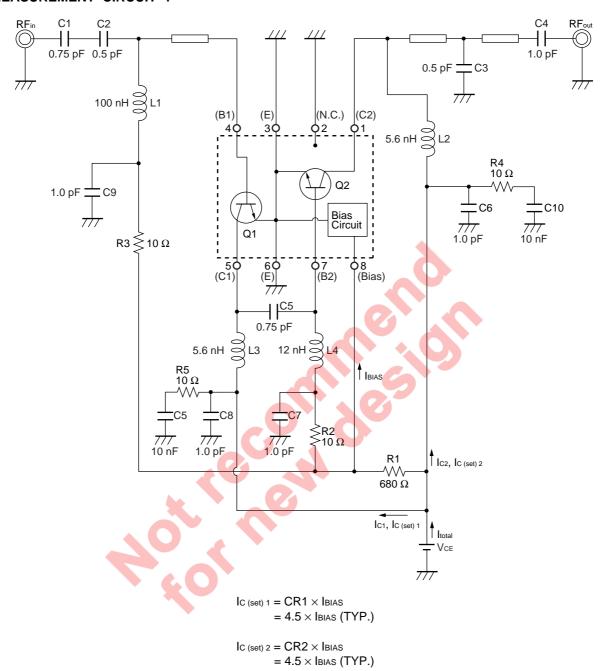
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Insertion Power Gain (Q2)	S <sub>21e</sub>   <sup>2</sup>	VcE = 3.6 V, Ic = 40 mA, f = 5.8 GHz	2	3.5	5	dB
Maximum Available Power Gain (Q2)	MAG2	VcE = 3.6 V, Ic = 40 mA, f = 5.8 GHz	8.5	10.0	10.5	dB
Output Power (Q2)	Pout2	VcE = 3.6 V, Ic (set) = 40 mA, f = 5.8 GHz, Pin = 11 dBm	17.5	19.0	-	dBm
Collector Current (Q2)	Icc2	VcE = 3.6 V, Ic (set) = 40 mA, f = 5.8 GHz, Pin = 11 dBm		70	-	mA

### (3) Q1 + Q2, 2 stage Amplifiers

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Output Power	Pout	$V_{\text{CE}} = 3.6 \text{ V}, \text{ R}_{\text{BIAS}} = 680 \ \Omega,$ f = 5.8 GHz, $P_{\text{In}} = -3 \text{ dBm}$ Note	17.5	19.0	-	mA
Total Current	Itotal	$V_{CE} = 3.6 \text{ V}, \text{ R}_{BIAS} = 680 \ \Omega,$ $f = 5.8 \ \text{GHz}, \text{ P}_{in} = -3 \ \text{dBm}$ Note	-	90	-	mA

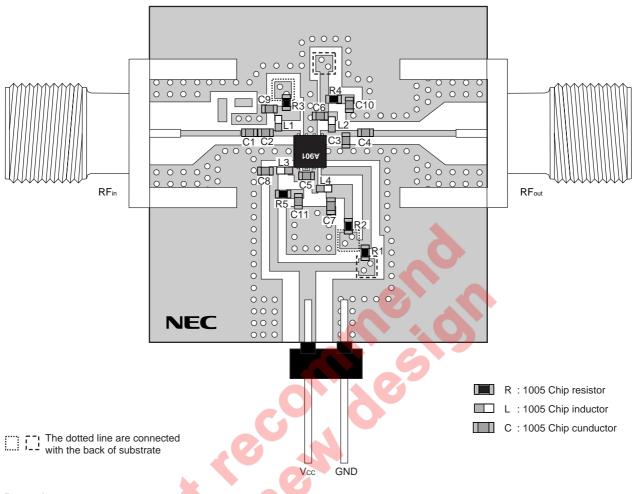
Note by MEASUREMENT CIRCUIT 1

### **MEASUREMENT CIRCUIT 1**



The application circuits and their parameters are for reference only and are not intended for use in actual design-ins.

### ILLUSTRATION OF THE TEST CIRCUIT ASSEMBLED ON EVALUATION BOARD



### Remarks

1. Substrate:  $20 \times 20 \times 0.8$  (t) mm FR-4 (4 Layer, each thickness 0.2 mm), copper thickness 18  $\mu$ m, gold flash plating

2. Back side : GND pattern

3. o: Through hole

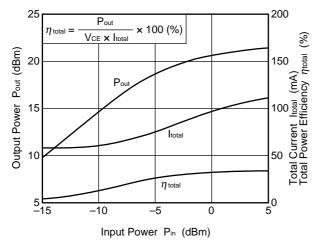
### USING THE NEC EVALUATION BOARD

Symbol	Values	Symbol	Values
R1	680 Ω	C2	0.5 pF
R2	10 Ω	C3	0.5 pF
R3	10 Ω	C4	1.0 pF
R4	10 Ω	C5	0.75 pF
R5	10 Ω	C6	1.0 pF
L1	100 nH	C7	1.0 pF
L2	5.6 nH	C8	1.0 pF
L3	5.6 nH	C9	1.0 pF
L4	12 nH	C10	10 nF
C1	0.75 pF	C11	10 nF

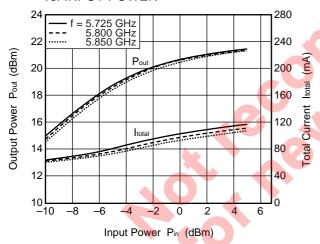
### TYPICAL CHARACTERISTICS

(TA = +25°C, VCE = 3.6 V, RBIAS = 680  $\Omega$ , f = 5.8 GHz, unless otherwise specified)

OUTPUT POWER, TOTAL CURRENT, TOTAL POWER EFFICIENCY vs. INPUT POWER

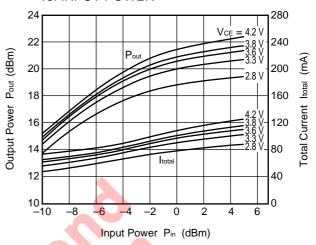


OUTPUT POWER, TOTAL CURRENT, vs. INPUT POWER

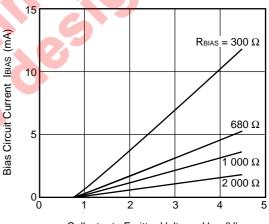


**Remark** The graphs indicate nominal characteristics.

OUTPUT POWER, TOTAL CURRENT, vs. INPUT POWER



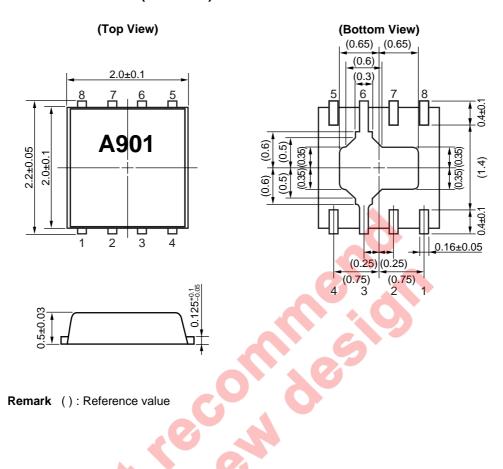
BIAS CIRCUIT CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



Collector to Emitter Voltage VcE (V)

### **PACKAGE DIMENSIONS**

### 8-PIN LEAD-LESS MINIMOLD (UNIT: mm)



NEC  $\mu$ PA901TU

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